

# **isc Silicon NPN Power Transistor**

# 2SC1431

### DESCRIPTION

- With TO-3 Package
- High voltage
- · Wide area of safe operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

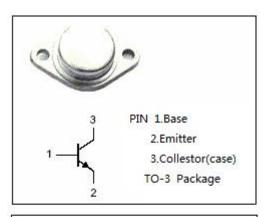
· Power amplifier applications

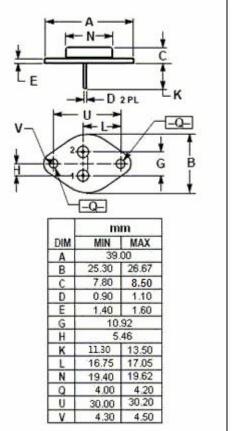
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL           | PARAMETER                    | VALUE   | UNIT |
|------------------|------------------------------|---------|------|
| V <sub>CBO</sub> | Collector-Base Voltage       | 110     | v    |
| V <sub>CEO</sub> | Collector-Emitter Voltage    | 110     | v    |
| V <sub>EBO</sub> | Emitter-Base Voltage         | 5       | V    |
| Ic               | Collector Current-Continuous | 2       | А    |
| Pc               | Collector Power Dissipation  | 23      | W    |
| TJ               | Junction Temperature         | -65~200 | °C   |
| T <sub>stg</sub> | Storage Temperature Range    | -65~200 | °C   |

#### **THERMAL CHARACTERISTICS**

| SYMBOL              | PARAMETER                            | МАХ | UNIT |  |
|---------------------|--------------------------------------|-----|------|--|
| R <sub>th j-c</sub> | Thermal Resistance, Junction to Case | 7.6 | °C/W |  |





isc website: www.iscsemi.com



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# **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL                | PARAMETER                            | CONDITIONS                                  | MIN | TYP. | мах | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------|
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =1.0A; I <sub>B</sub> = 0.1A |     |      | 1.0 | V    |
| V <sub>BE</sub> (sat) | Base-Emitter Saturation Voltage      | I <sub>C</sub> =1.0A; I <sub>B</sub> = 0.1A |     |      | 1.2 | V    |
| V <sub>(BR)CEO</sub>  | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = 10mA; I <sub>B</sub> = 0   | 110 |      |     | V    |
| V <sub>(BR)EBO</sub>  | Emitter-Base Breakdown Voltage       | I <sub>E</sub> = 1mA; I <sub>C</sub> = 0    | 5   |      |     | V    |
| h <sub>FE</sub>       | DC Current Gain                      | I <sub>C</sub> =0.4A; V <sub>CE</sub> = 2V  | 50  |      | 240 |      |
| Ісво                  | Collector Cutoff Current             | V <sub>CB</sub> = 110V ; I <sub>E</sub> = 0 |     |      | 100 | uA   |
| I <sub>EBO</sub>      | Emitter Cutoff Current               | V <sub>EB</sub> =5V; I <sub>C</sub> = 0     |     |      | 100 | uA   |



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